Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	5957	((438/229) or (438/230) or (438/231) or (438/232) or (438/299) or (438/301) or (438/303) or (438/305) or (438/306) or (438/307) or (438/364) or (438/366) or (438/595) or (438/682) or (438/755)).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/02 17:03
L2	108	1 and (l adj shap$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/02 17:03
L3	84	2 and (silicid$5)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/02 17:04
L4	5	("5153145" | "6297132" | "6380039" | "6432784" | "6506650").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2004/12/02 17:12
L5	3	("6417056" | "6429083" | "6432805").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2004/12/02 17:13
S1	0	((gate adj dielectric) with (semiconductor adj substrate)) same ((gate adj electrode) with (gate adj dielectric) with (semiconductor adj sustrate))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/05/10 14:46
S2	319	((gate adj dielectric) with (semiconductor adj substrate)) same ((gate adj electrode) with (gate adj dielectric) with (semiconductor adj substrate))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/05/10 14:34
S3	0	(((gate adj dielectric) with (semiconductor adj substrate)) same ((gate adj electrode) with (gate adj dielectric) with (semiconductor adj substrate))) and (extension adj control)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/05/10 14:06
S4	147	(((gate adj dielectric) with (semiconductor adj substrate)) same ((gate adj electrode) with (gate adj dielectric) with (semiconductor adj substrate))) and (protective adj layer$1 or (film$1))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/05/10 14:27

S5	0	(((((gate adj dielectric) with (semiconductor adj substrate)) same ((gate adj electrode) with (gate adj dielectric) with (semiconductor adj substrate))) and (extension adj control)) and (sidewall or (side adj wall) with protection)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/05/10 14:24
S6	0	(((((gate adj dielectric) with (semiconductor adj substrate)) same ((gate adj electrode) with (gate adj dielectric) with (semiconductor adj substrate))) and (extension adj control)) and (sidewall or (side adj wall))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/05/10 14:09
S7	12	(((((gate adj dielectric) with (semiconductor adj substrate)) same ((gate adj electrode) with (gate adj dielectric) with (semiconductor adj substrate))) and (protective adj layer$1 or (film$1))) and (first adj impurit$3) and (second adj impurit$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/05/10 14:11
S8	392	((gate adj dielectric) with (semiconductor adj substrate)) same ((gate adj electrode))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/05/10 14:18
S9	361	(((gate adj dielectric) same ((gate adj electrode)) with (semiconductor adj substrate)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/05/10 14:19
S10	333	(((gate adj dielectric) same (gate adj electrode)) with (semiconductor adj substrate))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/05/10 14:35
S11	333	((gate adj dielectric) same (gate adj electrode)) with (semiconductor adj substrate)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/05/10 14:24
S12	138	(((gate adj dielectric) same (gate adj electrode)) with (semiconductor adj substrate)) and (sidewall or (side adj wall))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/05/10 14:36
S13	72	((((gate adj dielectric) same (gate adj electrode)) with (semiconductor adj substrate)) and (sidewall or (side adj wall))) and (protective adj layer$1 or (film$1))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/05/10 14:37

S14	103052	(metal adj oxide adj field adj effect adj transistor$1 or (MOS adj transistor$1) or (MOSFET))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/06/17 13:35
S15	53	((metal adj oxide adj field adj effect adj transistor$1 or (MOS adj transistor$1) or (MOSFET))) same ((gate adj dielectric) with (semiconductor adj substrate)) same ((gate adj electrode) with (gate adj dielectric) with (semiconductor adj substrate))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/05/10 14:35
S16	62	((metal adj oxide adj field adj effect adj transistor$1 or (MOS adj transistor$1) or (MOSFET))) same(((gate adj dielectric) same (gate adj electrode)) with (semiconductor adj substrate))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/05/10 14:35
S17	0	(((((metal adj oxide adj field adj effect adj transistor$1 or (MOS adj transistor$1) or (MOSFET))) same(((gate adj dielectric) same (gate adj electrode)) with (semiconductor adj substrate))) same (sidewall or (side adj wall))) same (protective adj layer$1 or (film$1))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/05/10 14:38
S18	20	(((metal adj oxide adj field adj effect adj transistor$1 or (MOS adj transistor$1) or (MOSFET))) same(((gate adj dielectric) same (gate adj electrode)) with (semiconductor adj substrate))) and (sidewall or (side adj wall))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/05/10 14:37
S19	0	(((((metal adj oxide adj field adj effect adj transistor$1 or (MOS adj transistor$1) or (MOSFET))) same(((gate adj dielectric) same (gate adj electrode)) with (semiconductor adj substrate))) same (sidewall or (side adj wall))) and (protective adj layer$1 or (film$1))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/05/10 14:40
S20	2	(((metal adj oxide adj field adj effect adj transistor$1 or (MOS adj transistor$1) or (MOSFET))) same(((gate adj dielectric) same (gate adj electrode)) with (semiconductor adj substrate))) same (sidewall or (side adj wall))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/05/10 14:49

S21	2	(((((metal adj oxide adj field adj effect adj transistor$1 or (MOS adj transistor$1) or (MOSFET))) same(((gate adj dielectric) same (gate adj electrode)) with (semiconductor adj substrate))) same (sidewall or (side adj wall)) and ((protective or (insulat$3)) adj layer$1 or (film$1))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/05/10 14:48
S22	6770	gate adj dielectric	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/05/10 14:47
S23	2280	(gate adj dielectric) same (gate adj electrode)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/05/10 14:48
S24	803	((gate adj dielectric) same (gate adj electrode)) same ((protective or (insulat$3)) adj layer$1 or (film$1))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/05/10 14:49
S25	138	(((gate adj dielectric) same (gate adj electrode)) same ((protective or (insulat$3)) adj layer$1 or (film$1))) same (sidewall or (side adj wall))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/05/10 14:50
S26	7	(((((gate adj dielectric) same (gate adj electrode)) same ((protective or (insulat$3)) adj layer$1 or (film$1))) same (sidewall or (side adj wall))) same (sidewall or (side adj wall) adj mask$1)) same (ion adj implant$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/05/10 14:53
S27	105	((((gate adj dielectric) same (gate adj electrode)) same ((protective or (insulat$3)) adj layer$1 or (film$1))) same (sidewall or (side adj wall))) same (sidewall or (side adj wall) adj mask$1)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/05/10 14:54
S28	2009	((438/301) or (438/303) or (438/305)).CCLS.	US-PGPUB; USPAT; USOCR	OR	OFF	2004/06/17 15:22
S29	2774	((438/301) or (438/303) or (438/305)).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/05/15 11:53

S30	0	(((438/301) or (438/303) or (438/305)).CCLS.) and (dual adj spacer) same (implant$3 with extension)	US-PGPUB; USPAT	OR	OFF	2002/05/15 11:54
S31	0	(((438/301) or (438/303) or (438/305)).CCLS.) and (dual adj spacer) same (implant$3 with extension)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/05/15 11:56
S32	1	("6287920").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2002/05/15 11:56
S33	130	(((438/301) or (438/303) or (438/305)).CCLS.) and (implant$3 with extension)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/05/15 13:51
S34	117	(mos adj transisor) or (metal adj oxide adj transistor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/05/16 17:05
S35	297	((mos adj transisor) or (metal adj oxide adj transistor)) with (plural adj dop$3) or ((first adj dop$3) with (second adj dop$3) with (third adj dop$3))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/05/16 17:08
S36	4	(((mos adj transisor) or (metal adj oxide adj transistor)) with (plural adj dop$3) or ((first adj dop$3) with (second adj dop$3) with (third adj dop$3))) with (ion adj implant$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/05/16 17:10
S37	6	(((mos adj transisor) or (metal adj oxide adj transistor)) with (plural adj dop$3) or ((first adj dop$3) with (second adj dop$3) with (third adj dop$3))) with extension	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/05/16 17:10
S38	11	l adj shap$2 with sidewall$1 and extension$1 and implant$3 and dop$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/10/10 11:23
S39	5	l adj shap$2 with sidewall$1 and extension$1 and implant$3 and dop$3 and boron	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/10/09 18:16

S40	16	I adj shap$2 with sidewall$1 and implant$3 and dop$3 and boron	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/10/09 18:16
S41	0	I adj shap$2 with sidewall$1 and implant$3 and dop$3 and boron and boron adj florine	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/10/10 11:24
S42	16	I adj shap$2 with sidewall$1 and implant$3 and dop$3 and boron	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/10/10 11:27
S43	156	I adj shap$2 and implant$3 and dop$3 and boron	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/10/10 11:28
S44	68	I adj shap$2 and mos and implant$3 and dop$3 and boron	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/10/10 11:49
S45	166723	I adj shap$2 mdd with implant$3 and boron	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/10/10 11:50
S46	1	I adj shap$2 and mdd with implant$3 and boron	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/10/10 11:51
S47	0	I adj shap$2 with side adj wall$ and mdd with implant$3 and boron	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/10/10 11:52
S48	21	mos and mdd with implant$3 and boron	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/10/10 11:52
S49	15	pmos and mdd and boron	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/10/10 12:42
S50	56729	anisotrop$$5	US-PGPUB; USPAT	OR	ON	2003/02/21 17:28

S51	3	isotrop$5	US-PGPUB; USPAT	OR	ON	2003/02/21 17:28
S52	28701	isotrop$5	US-PGPUB; USPAT	OR	ON	2004/06/17 18:42
S53	15001	anisotrop$$5 and isotrop$5	US-PGPUB; USPAT	OR	ON	2003/02/21 17:29
S54	342575	gate	US-PGPUB; USPAT	OR	ON	2003/02/21 17:29
S55	4331	(anisotrop$$5 and isotrop$5) and gate	US-PGPUB; USPAT	OR	ON	2003/02/21 17:30
S56	39483	ion adj implant$5	US-PGPUB; USPAT	OR	ON	2003/02/21 17:30
S57	1875	((anisotrop$$5 and isotrop$5) and gate) and (ion adj implant$5)	US-PGPUB; USPAT	OR	ON	2003/02/21 17:30
S58	432112	extension	US-PGPUB; USPAT	OR	ON	2003/02/21 17:31
S59	367	(((anisotrop$$5 and isotrop$5) and gate) and (ion adj implant$5)) and extension	US-PGPUB; USPAT	OR	ON	2003/02/21 17:31
S60	9	("4908326" | "5234850" | "5501997" | "5541132" | "5679589" | "5770508" | "5783475" | "5863824" | "6020242").PN.	USPAT	OR	OFF	2003/02/21 17:57
S61	2768	l adj shap$2 same spacer$1	US-PGPUB; USPAT	OR	OFF	2004/06/17 18:43
S62	5	((((anisotrop$$5 and isotrop$5) and gate) and (ion adj implant$5)) and extension) and (l adj shap$2 same spacer$1)	US-PGPUB; USPAT	OR	OFF	2003/02/21 18:01
S63	42115	anisotropic or anisotropical	US-PGPUB; USPAT	OR	ON	2003/05/14 09:51
S64	29071	isotropic or isotropical	US-PGPUB; USPAT	OR	ON	2003/05/14 09:52
S65	7380	(anisotropic or anisotropical) same (isotropic or isotropical)	US-PGPUB; USPAT	OR	ON	2003/05/14 09:53
S66	2340873	side adj wall or side	US-PGPUB; USPAT	OR	ON	2003/05/14 09:53
S67	185606	mask	US-PGPUB; USPAT	OR	ON	2003/05/14 09:53
S68	7009	(side adj wall or side) near2 mask	US-PGPUB; USPAT	OR	ON	2003/05/14 09:54
S69	234	((anisotropic or anisotropical) same (isotropic or isotropical)) and ((side adj wall or side) near2 mask)	US-PGPUB; USPAT	OR	ON	2003/05/14 09:54
S70	3	("5770508" | "5783475" | "5817563").PN.	USPAT	OR	OFF	2003/05/14 09:57

S71	6	("4784965" | "4855247" | "5024959" | "5153145" | "5234850" | "5472896").PN.	USPAT	OR	OFF	2003/05/14 09:58
S72	19	"5770508".URPN.	USPAT	OR	OFF	2003/05/14 09:59
S73	2	"6197648".URPN.	USPAT	OR	OFF	2003/05/14 10:01
S74	3802	l adj shap$2 same spacer$1	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/06/17 13:21
S75	424360	(metal adj oxide adj field adj effect adj transistor$1)or MOS or MOSFET	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/06/17 13:36
S76	195	(l adj shap$2 same spacer$1) and ((metal adj oxide adj field adj effect adj transistor$1)or MOS or MOSFET)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/06/17 13:37
S77	4822	((438/229) or (438/230) or (438/231) or (438/232) or (438/301) or (438/303) or (438/305) or (438/306) or (438/307) or (438/595)).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/06/17 18:43
S78	65	(((438/229) or (438/230) or (438/231) or (438/232) or (438/301) or (438/303) or (438/305) or (438/306) or (438/307) or (438/595)).CCLS.) and (l adj shap$2 same spacer$1)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/06/17 15:28
S79	49892	isotrop$5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/06/17 18:43
S80	3802	l adj shap$2 same spacer$1	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/06/17 18:45
S81	4822	((438/229) or (438/230) or (438/231) or (438/232) or (438/301) or (438/303) or (438/305) or (438/306) or (438/307) or (438/595)).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/02 16:58

S82	13856	isotrop$5 near5 etch$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/06/17 18:44
S83	52320	(isotrop$5 or wet) near5 etch$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/06/17 18:48
S84	54	((isotrop$5 or wet) near5 etch$3) same (l adj shap$2 same spacer$1)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/06/17 18:44
S85	346624	spacer$1	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/06/17 18:45
S86	3851	((isotrop$5 or wet) near5 etch$3) same spacer$1	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/06/17 18:45
S87	189323	l adj shap$2	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/06/17 18:46
S88	54	(((isotrop$5 or wet) near5 etch$3) same spacer$1) same (l adj shap$2)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/06/17 18:48
S89	23	((((isotrop$5 or wet) near5 etch$3) same spacer$1) same (l adj shap$2)) and ((isotrop$5 or wet) near5 etch$3 near10 nitride)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/06/17 18:49
S90	2	"6518136"	USPAT	OR	OFF	2004/06/17 19:07
S91	3	("5716862" | "6025267" | "6165826").PN.	USPAT	OR	OFF	2004/06/17 19:12
S92	13	("4038107" | "4638347" | "4697199" | "4735680" | "4764477" | "4818714" | "4843023" | "4851730" | "4853352" | "4981810" | "5183770" | "5221632" | "5256586").PN.	USPAT	OR	OFF	2004/06/17 19:35
S93	41	"5573965".URPN.	USPAT	OR	OFF	2004/06/17 19:35